

## **Fast Recovery Diode**

Supersedes July 1996 version, DS4412 - 1.2

DS4412 - 1.3 March 1998

#### **APPLICATIONS**

■ Snubber Diode For GTO Applications.

# $\begin{array}{ccc} \text{KEY PARAMETERS} \\ \text{V}_{\text{RRM}} & 3500\text{V} \\ \text{I}_{\text{F(AV)}} & 335\text{A} \\ \text{I}_{\text{FSM}} & 3500\text{A} \\ \text{Q}_{\text{r}} & 400\mu\text{C} \\ \text{t}_{\text{--}} & 4.0\mu\text{s} \end{array}$

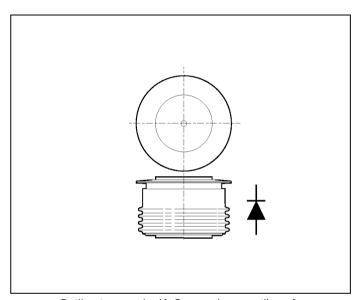
#### **FEATURES**

- Double side cooling.
- High surge capability.
- Low recovery charge.

#### **VOLTAGE RATINGS**

Type Number	Repetitive Peak Reverse Voltage V <sub>RRM</sub> V	Conditions
DSF8035SK35	3500	V <sub>RSM</sub> = V <sub>RRM</sub> + 100V

Lower voltage grades available.



Outline type code: K. See package outlines for further information.

#### **CURRENT RATINGS**

Symbol	Parameter	Conditions	Max.	Units		
Double Side Cooled						
I <sub>F(AV)</sub>	Mean forward current	Half wave resistive load, T <sub>case</sub> = 65°C	335	Α		
I <sub>F(RMS)</sub>	RMS value	$T_{case} = 65^{\circ}C$	529	Α		
I <sub>F</sub>	Continuous (direct) forward current	T <sub>case</sub> = 65°C	490	Α		
Single Side Cooled (Anode side)						
I <sub>F(AV)</sub>	Mean forward current	Half wave resistive load, T <sub>case</sub> = 65°C	226	Α		
I <sub>F(RMS)</sub>	RMS value	T <sub>case</sub> = 65°C	355	Α		
I <sub>F</sub>	Continuous (direct) forward current	T <sub>case</sub> = 65°C	317	Α		

### **SURGE RATINGS**

Symbol	Parameter	Conditions	Max.	Units
I <sub>FSM</sub>	Surge (non-repetitive) forward current	10mc half cine; with 09/ V T = 150°C	3.0	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	10ms half sine; with 0% V <sub>RRM.</sub> T <sub>j</sub> = 150°C	45 x 10 <sup>3</sup>	A <sup>2</sup> s
I <sub>FSM</sub>	Surge (non-repetitive) forward current	10me half aine; with 50% V T 150%	2.4	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	10ms half sine; with 50% V <sub>RRM,</sub> T <sub>j</sub> = 150°C	28.8 x 10 <sup>3</sup>	A <sup>2</sup> s

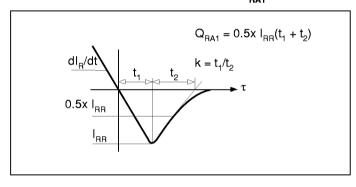
#### THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
	Thermal resistance - junction to case	Double side cooled	dc	-	0.048	°C/W
R <sub>th(j-c)</sub>		Single side cooled	Anode dc	-	0.090	°C/W
			Cathode dc	-	0.103	°C/W
R <sub>th(c-h)</sub>	Thermal resistance - case to heatsink	Clamping force 8.0kN with mounting compound	Double side	-	0.01	°C/W
			Single side	-	0.02	°C/W
T <sub>vj</sub>	Virtual junction temperature	Forward (conducting)		-	150	°C
T <sub>stg</sub>	Storage temperature range			-55	175	°C
-	Clamping force			7.0	9.0	kN

#### **CHARACTERISTICS**

Symbol	Parameter	Conditions	Тур.	Max.	Units
V <sub>FM</sub>	Forward voltage	At 400A peak, T <sub>case</sub> = 25°C	-	3.5	>
I <sub>RRM</sub>	Peak reverse current	At V <sub>RRM</sub> , T <sub>case</sub> = 150°C	-	50	mA
t <sub>rr</sub>	Reverse recovery time		-	4.0	μs
Q <sub>RA1</sub>	Recovered charge (50% chord)	$I_{\rm F} = 1000$ A, di <sub>RR</sub> /dt = 100A/ $\mu$ s	-	400	μС
I <sub>RM</sub>	Reverse recovery current	$T_{case} = 150$ °C, $V_{R} = 100$ V	-	220	Α
К	Soft factor		1.4	-	-
V <sub>TO</sub>	Threshold voltage	At T <sub>vj</sub> = 150°C	-	1.8	٧
r <sub>T</sub>	Slope resistance	At T <sub>vj</sub> = 150°C	-	3.7	mΩ
V <sub>FRM</sub>	Forward recovery voltage	di/dt = 1000A/μs, T <sub>j</sub> = 125°C	-	140	V

# DEFINITION OF K FACTOR AND $\mathbf{Q}_{\text{RA1}}$



#### **CURVES**

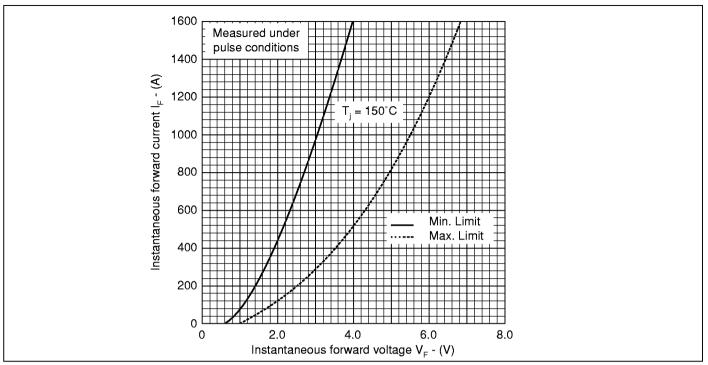


Fig.1 Maximum (limit) forward characteristics

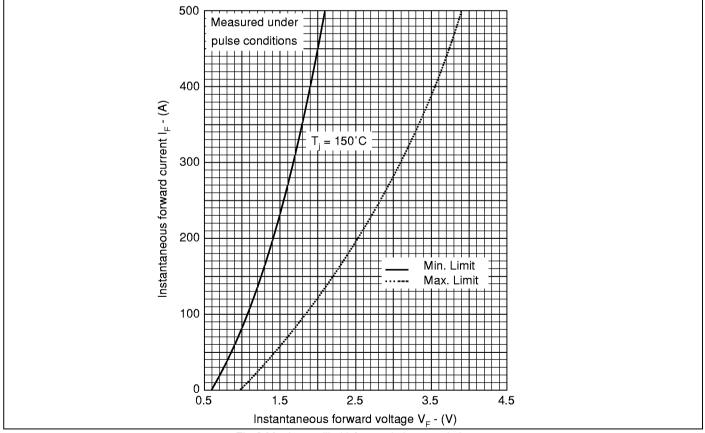


Fig.2 Maximum (limit) forward characteristics

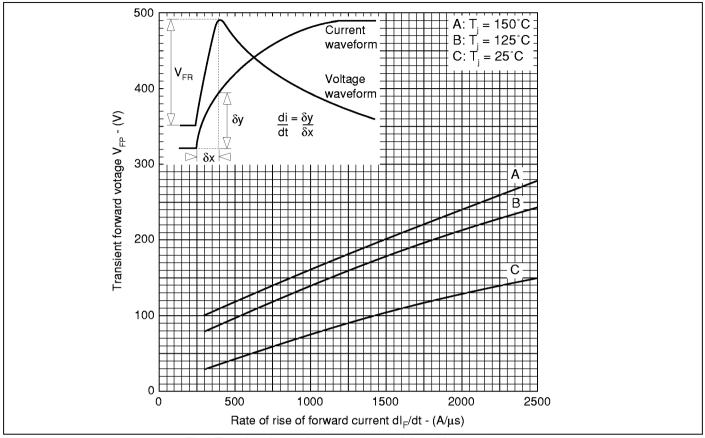


Fig.3 Transient forward voltage vs rate of rise of forward current

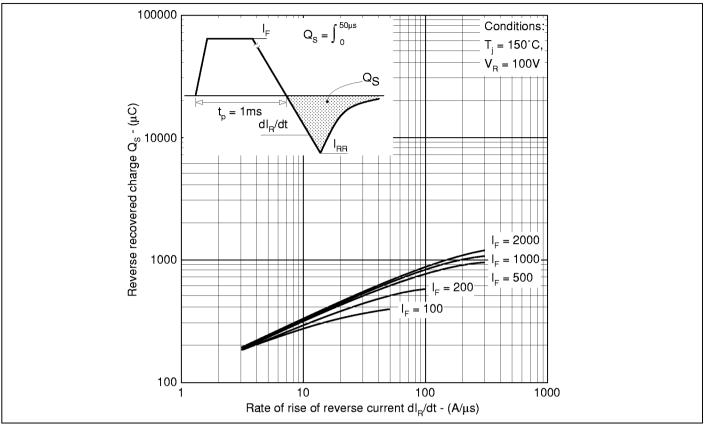


Fig. 4 Recovered charge

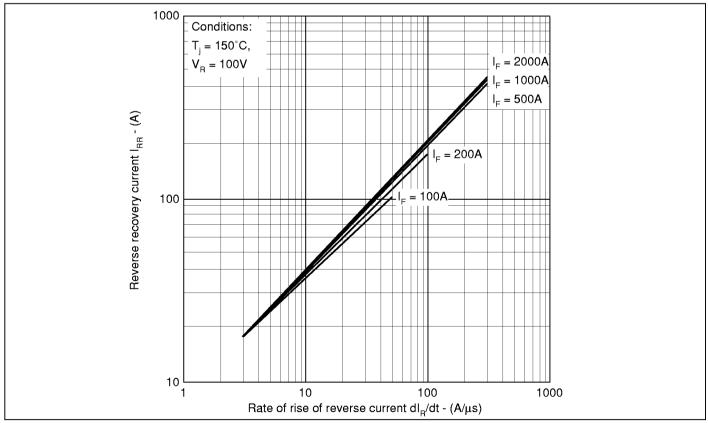


Fig. 5 Typical reverse recovery current vs rate of rise of reverse current

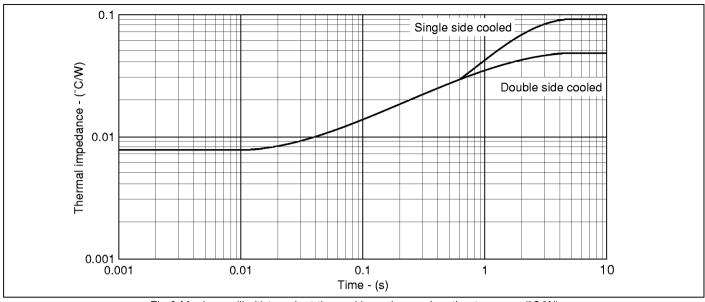
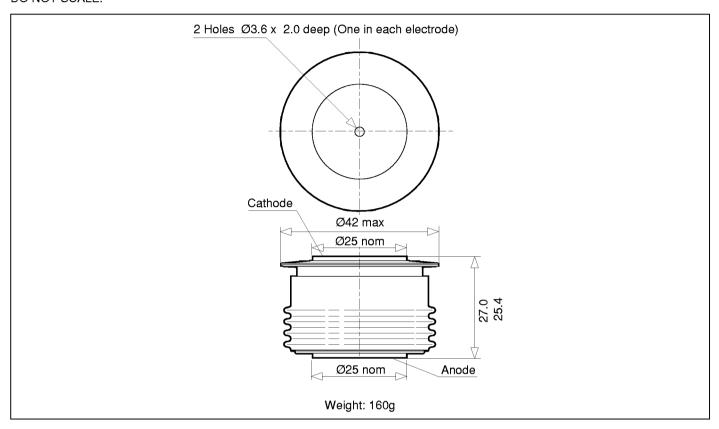


Fig.6 Maximum (limit) transient thermal impedance - junction to case - (°C/W)

#### **PACKAGE DETAILS - K**

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





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